

In the Claims:

Please amend claim 3-4, 6 and 9 as indicated below. This listing of claims replaces all prior versions.

1. (Original) An electronic device comprising a semiconductor substrate having a first and a second side and provided with a capacitor and a vertical interconnect through the substrate extending from the first to the second side, on which first side the capacitor is present, characterized in that the capacitor is a vertical trench capacitor provided with a plurality of trenches in which a layer of dielectric material is present between a first and a second conductive surface, said layer of dielectric material also being used as insulation between the substrate and the vertical interconnect.

2. (Original) An electronic device as claimed in Claim 1, wherein the vertical interconnect has a first part and a second part, which first part is exposed on the first side of the substrate, is narrower than the second part and has a substantially cylindrical shape.

3. (Currently amended) An electronic device as claimed in Claim 1, characterized in that ~~the trenches of the vertical interconnect~~ includes a plurality of parallel trenches each of which is substantially filled with electrically conductive material.

4. (Currently amended) An electronic device as claimed in Claim 2, characterized in that the first part of the vertical interconnect comprises a plurality of parallel through-holes that extend from the first side of the substrate to the second part of the vertical interconnect through the substrate, each of the plurality of parallel through-holes being substantially ~~which~~ is filled with electrically conductive material.

5. (Original) An electronic device as claimed in Claim 1, characterized in that:

- contact pads for coupling to an external carrier are present on the second side;
- a first vertical interconnect is used for grounding and
- a second interconnect is used for signal transmission.

6. (Currently amended) An electronic device as claimed in Claim 5 [[4]], characterized in that the first and second vertical interconnect are designed so as to form a coaxial structure.

7. (Original) An electronic device as claimed in Claim 1, characterized in that an integrated circuit is defined on the second side of the substrate.

8. (Original) An electronic device as claimed in Claim 1, characterized in that the substrate comprises a high-ohmic zone which is present adjacent to the vertical capacitors and acts as a protection against parasitic currents.

9. (Currently amended) An electronic device as claimed in Claim 8 [[1]], characterized in that a planar capacitor is present on the first side of the substrate, which planar capacitor comprises the same layer of dielectric material as the vertical capacitor, and wherein the high-ohmic zone separates the planar capacitor from the vertical trench capacitor.

10. (Previously presented) An assembly comprising the electronic device of claim 1, and a semiconductor device, which semiconductor device is electrically connected to bond pads present on the first side of the substrate.

11-19. (Cancelled)